TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type

# 2SK2162

### Audio-Frequency Power Amplifier Applications

High breakdown voltage: V<sub>DSS</sub> = 180 V

High forward transfer admittance:  $|Y_{fs}| = 0.7 \text{ S (typ.)}$ 

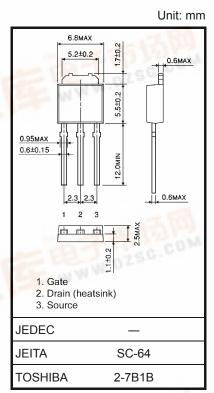
Complementary to 2SJ338

### Absolute Maximum Ratings (Ta = 25°C)

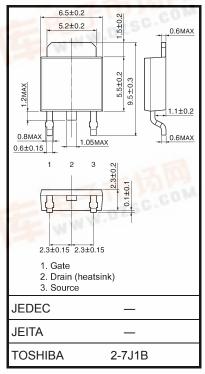
Characteristic	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	180	V
Gate-source voltage	V <sub>GSS</sub>	±20	٧
Drain current (Note 1)	I <sub>D</sub>	1	А
Power dissipation (Tc = 25°C)	$P_{D}$	20	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	<b>−55~150</b>	°C

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.36 g (typ.)



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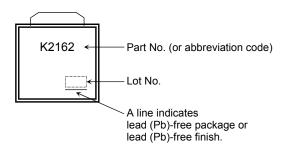
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## **Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	_	_	±100	nA
Drain-source breakdown voltage	V (BR) DSS	$I_D = 10$ mA, $V_{GS} = 0$ V	180	_	_	V
Gate-source cutoff current	V <sub>GS</sub> (OFF)	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10 mA	1.4	_	2.8	٧
Drain-source saturation voltage	V <sub>DS</sub> (ON)	$I_D = 0.6 \text{ A}, V_{GS} = 10 \text{ V}$	_	1.7	3.0	٧
Forward transfer admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_D = 0.3 \text{ A}$	_	0.7	_	S
Input capacitance	C <sub>iss</sub>		_	170	_	pF
Output capacitance	Coss	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	45	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	17	_	pF

This transistor is an electrostatic-sensitive device. Handle with care.

### Marking



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20070701-EN

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